

PATENT NUMBER

O.I.P.E.

SCANNED

O.I.P.E.

34

PATENT DATE

04

CR

APPLICATION NO.
09/925080

CONT/PRIOR	
D	F

CLASS
438

SUBCLASS

ART UNIT

EXAMINER

APPLICANTS

Ferruccio Frisina

NAME

Method of manufacturing an integrated edge structure for high voltage semiconductor devices, and related integrated edge structure

PTO-2040
12/09

ISSUING CLASSIFICATION

[illegible]

☒ Continued on inside cover

TERMINAL
DISCUSSION

DRAWINGS

CLASSES ALLOWED

The term of this patent
subsequent to _____ (date)
has been disclaimed.

☐ The term of this patent shall not extend beyond the expiration date of U.S. Patent No.

☐ The terminal _____ months of this patent have been disclaimed.

(Assistant Examiner)

(Data)

(Prison, England)

Legal Instruments Examined

NOTICE OF ADVANCE MAILING

ISSUE FEE

Amount:

Date Recd:

ISSUE BATCH NUMBER

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(Attached in packet on first meeting)

(FACE)